

CD54/74HC280
CD54/74HCT280

HARRIS SEMICONDUCTOR

27E D



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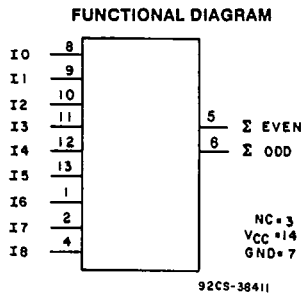
9



HAS

High-Speed CMOS Logic

T-45-17-00



9-Bit Odd/Even Parity Generator/Checker

Type Features:

- Typical propagation delay = 17ns @ $V_{CC} = 5V$, $C_L = 15pF$, $T_A = 25^\circ C$
- Replaces 74LS180 types
- Easily cascadable

Family Features:

- Fanout (Over Temperature Range):
Standard Outputs - 10 LSTTL Loads
Bus Driver Outputs - 15 LSTTL Loads

- Wide Operating Temperature Range:
CD74HC/HCT: -40 to $+85^\circ C$
- Balanced Propagation and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types:
2 to 6 V Operation
High Noise Immunity: $N_{IL} = 30\%$, V_{CC} ,
 $N_{IH} = 30\%$ of V_{CC} @ $V_{CC} = 5V$

The RCA-CD54/74HC280 and CD54/74HCT280 are 9-bit odd/even parity, generator checker devices. Both even and odd parity outputs are available for checking or generating parity for words up to nine bits long. Even parity is indicated (ΣE output is high) when an even number of data inputs is high. Odd parity is indicated (ΣO output is high) when an odd number of data inputs is high. Parity checking for words larger than 9 bits can be accomplished by tying the

ΣE output to any input of an additional HC/HCT280 parity checker.

The CD54HC280 and CD54HCT280 are supplied in 14-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC280 and CD74HCT280 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

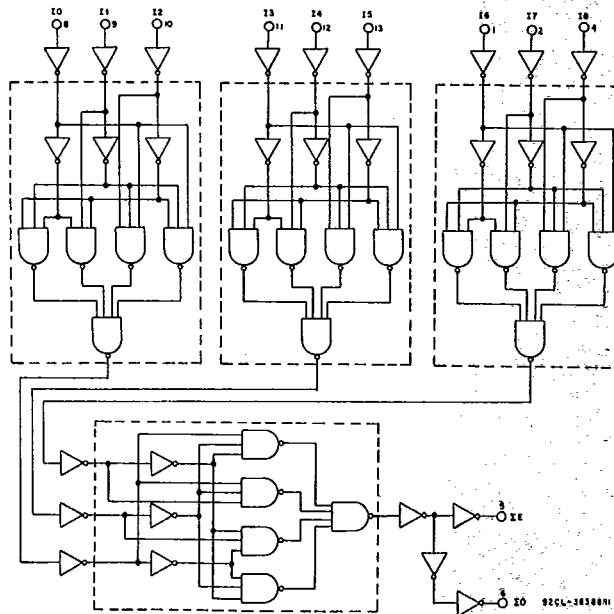


Fig. 1 — Logic Diagram

CD54/74HC280
CD54/74HCT280

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (V_{CC}):
(Voltages referenced to ground) -0.5 to + 7 V

DC INPUT DIODE CURRENT, I_{IK} (FOR V_i < -0.5 V OR V_i ~ V_{CC} + 0.5V) ±20mA

DC OUTPUT DIODE CURRENT, I_{OK} (FOR V_o < -0.5 V OR V_o > V_{CC} + 0.5V) ±20mA

DC DRAIN CURRENT, PER OUTPUT (I_O) (FOR -0.5 V < V_o < V_{CC} + 0.5V) ±25mA

DC V_{CC} OR GROUND CURRENT (I_{CC}) ±50mA

POWER DISSIPATION PER PACKAGE (P_D):

For T_A = -40 to +60°C (PACKAGE TYPE E) 500 mW

For T_A = +60 to +85°C (PACKAGE TYPE E) Derate Linearly at 8 mW/°C to 300 mW

For T_A = -55 to +100°C (PACKAGE TYPE F, H) 500 mW

For T_A = +100 to +125°C (PACKAGE TYPE F, H) Derate Linearly at 8 mW/°C to 300 mW

For T_A = -40 to +70°C (PACKAGE TYPE M) 400 mW

For T_A = +70 to +125°C (PACKAGE TYPE M) Derate Linearly at 6 mW/°C to 70 mW

OPERATING-TEMPERATURE RANGE (T_A):

PACKAGE TYPE F, H -55 to +125°C

PACKAGE TYPE E, M -40 to +85°C

STORAGE TEMPERATURE (T_{stg}) -65 to +150°C

LEAD TEMPERATURE (DURING SOLDERING):

At distance 1/16 ± 1/32 in. (1.59 ± 0.79 mm) from case for 10 s max. +265°C

Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm) with solder contacting lead tips only +300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} .*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	
DC Input or Output Voltage V _{IN} , V _{OUT}	0	V _{CC}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	
Input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	ns
at 4.5 V	0	500	
at 6 V	0	400	

*Unless otherwise specified, all voltages are referenced to Ground.

HARRIS SEMICONDUCTOR SECTOR 27E D 430227J 00J7755 0 HAS

CD54/74HC280 CD54/74HCT280

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CD74HC280/CD54HC280										CD74HCT280/CD54HCT280										UNITS				
	TEST CONDITIONS			74HC/54HC SERIES			74HC SERIES			54HC SERIES			TEST CONDITIONS			74HCT/54HCT SERIES			74HCT SERIES			54HCT SERIES			
	V _i V	I _o mA	V _{cc} V	+25°C			-40/ +85°C			-55/ +125°C			V _i V	V _{cc} V	+25°C			-40/ +85°C				-55/ +125°C			
				Min	Typ	Max	Min	Max	Min	Max	Min	Max			Min	Typ	Max	Min	Max	Min		Max			
High-Level Input Voltage V _{ih}			2	1.5	—	—	1.5	—	1.5	—	—	4.5	to	2	—	—	2	—	2	—	—	V			
			4.5	3.15	—	—	3.15	—	3.15	—	—	5.5													
			6	4.2	—	—	4.2	—	4.2	—															
Low-Level Input Voltage V _{il}			2	—	—	0.5	—	0.5	—	0.5	—	4.5	to	—	—	0.8	—	0.8	—	0.8	—	V			
			4.5	—	—	1.35	—	1.35	—	1.35	—	5.5													
			6	—	—	1.8	—	1.8	—	1.8	—														
High-Level Output Voltage V _{oh}	V _L or V _{oh}	-0.02	2	1.9	—	—	1.9	—	1.9	—	V _K or V _{oh}	4.5	4.4	—	—	4.4	—	4.4	—	4.4	—	V			
CMOS Loads			4.5	4.4	—	—	4.4	—	4.4	—															
			6	5.9	—	—	5.9	—	5.9	—															
TTL Loads	V _K or V _{oh}										V _K or V _{oh}	4.5	3.98	—	—	3.84	—	3.7	—	—	—	V			
		-4	4.5	3.98	—	—	3.84	—	3.7	—															
		-5.2	6	5.48	—	—	5.34	—	5.2	—															
Low-Level Output Voltage V _{ol}	V _L or V _{oh}	0.02	2	—	—	0.1	—	0.1	—	0.1	V _L or V _{oh}	4.5	—	—	0.1	—	0.1	—	0.1	—	0.1	V			
CMOS Loads			4.5	—	—	0.1	—	0.1	—	0.1															
			6	—	—	0.1	—	0.1	—	0.1															
TTL Loads	V _L or V _{oh}										V _L or V _{oh}	4.5	—	—	0.26	—	0.33	—	0.4	—	—	V			
		4	4.5	—	—	0.26	—	0.33	—	0.4															
		5.2	6	—	—	0.26	—	0.33	—	0.4															
Input Leakage Current I _i	V _{cc} or Gnd		6	—	—	±0.1	—	±1	—	±1	Any Voltage Between V _{cc} & Gnd	5.5	—	—	±0.1	—	±1	—	±1	—	±1	μA			
Quiescent Device Current I _{cc}	V _{cc} or Gnd	0	6	—	—	8	—	80	—	160	V _{cc} or Gnd	5.5	—	—	8	—	80	—	160	—	160	μA			
Additional Quiescent Device Current per input pin: 1 unit load ΔI _{cc} *											V _{cc} -2.1 to 5.5	4.5	—	100	360	—	450	—	490	—	490	μA			

*For dual-supply systems theoretical worst case (V_i = 2.4 V, V_{cc} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
ALL	1

*Unit Load is ΔI_{cc} limit specified in Static Characteristic Chart, e.g., 360 μA max. @ 25°C.

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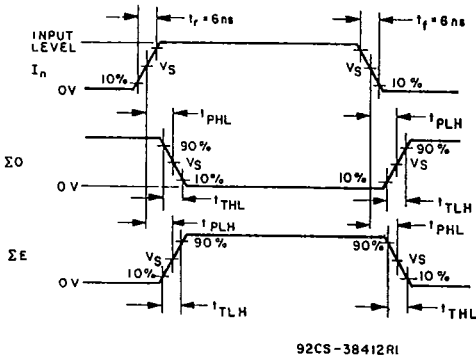
SWITCHING CHARACTERISTICS ($V_{CC} = 5\text{ V}$, $T_A = 25^\circ\text{C}$, Input $t_r, t_f = 6\text{ ns}$)

CHARACTERISTIC	C_L (pF)	SYMBOL	TYPICAL		UNITS
			HC	HCT	
Propagation Delay Any Input to ΣO	15	t_{PHL}	17	19	ns
		t_{PLH}	17	18	
Power Dissipation Capacitance*	—	C_{PD}	58	58	pF

* C_{PD} is used to determine the dynamic power consumption, per package.
 $PD = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = input frequency,
 C_L = output load capacitance,
 V_{CC} = supply voltage

SWITCHING CHARACTERISTICS ($C_L = 50\text{ pF}$, Input $t_r, t_f = 6\text{ ns}$)

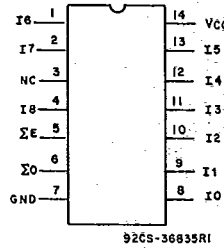
CHARACTERISTIC	SYMBOL	V_{CC}	25°C				-40°C to +85°C				-55°C to +125°C				UNITS
			HC		HCT		74HC		74HCT		54HC		54HCT		
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay, Any Input to ΣO	t_{PLH}	2	—	200	—	—	—	250	—	—	—	300	—	—	ns
	t_{PHL}	4.5	—	40	—	45	—	50	—	56	—	60	—	68	
		6	—	34	—	—	—	43	—	—	—	51	—	—	
Any Input to ΣE	t_{PLH}	2	—	200	—	—	—	250	—	—	—	300	—	—	ns
	t_{PHL}	4.5	—	40	—	42	—	50	—	53	—	60	—	63	
		6	—	34	—	—	—	43	—	—	—	51	—	—	
Output Transition Time	t_{TLH}	2	—	75	—	—	—	95	—	—	—	110	—	—	ns
	t_{THL}	4.5	—	15	—	15	—	19	—	19	—	22	—	22	
		6	—	13	—	—	—	16	—	—	—	19	—	—	
Input Capacitance	C_i		—	10	—	10	—	10	—	10	—	10	—	10	pF



92CS-38412RI

	54/74HC	54/74HCT
INPUT LEVEL	V_{CC}	3 V
SWITCHING VOLTAGE, V_S	50% V_{CC}	1.3 V

Fig. 2 — Propagation delay and transition times.



92CS-36835RI

TERMINAL ASSIGNMENT

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